Silicon P-Channel MOS FET

HITACHI

Application

Low frequency power amplifier

Complementary pair with 2SK1056, 2SK1057 and 2SK1058

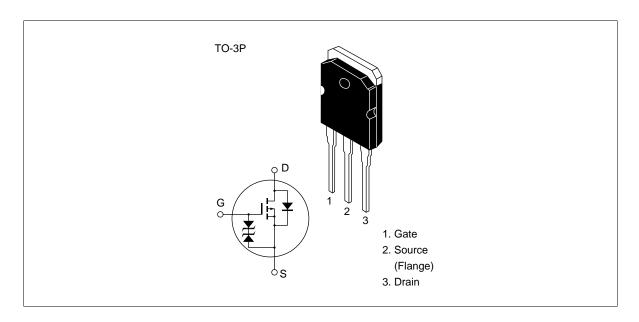
Features

- Good frequency characteristic

 High speed switch
- High speed switching
- Wide area of safe operation
- Enhancement-mode
- Good complementary characteristics
- Equipped with gate protection diodes
- Suitable for audio power amplifier



Outline



Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

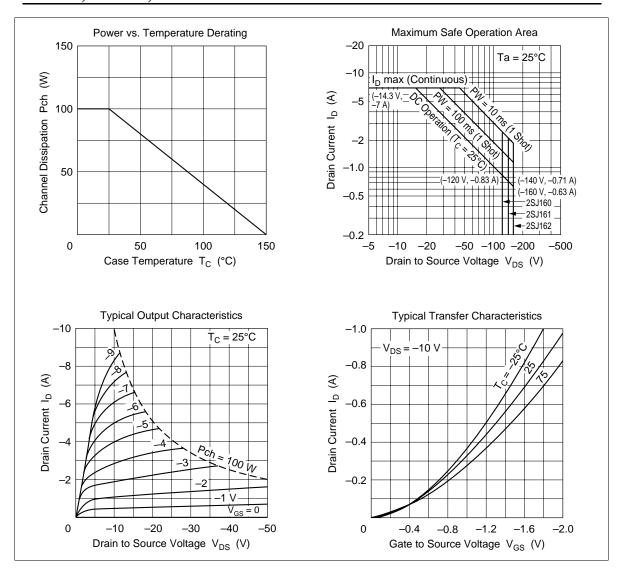
Item		Symbol	Ratings	Unit
Drain to source voltage	2SJ160	$V_{\scriptscriptstyle DSX}$	-120	V
	2SJ161		-140	
	2SJ162		-160	
Gate to source voltage		$V_{\sf GSS}$	±15	V
Drain current		I _D	- 7	Α
Body to drain diode reverse drain current		I _{DR}	- 7	А
Channel dissipation		Pch*1	100	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

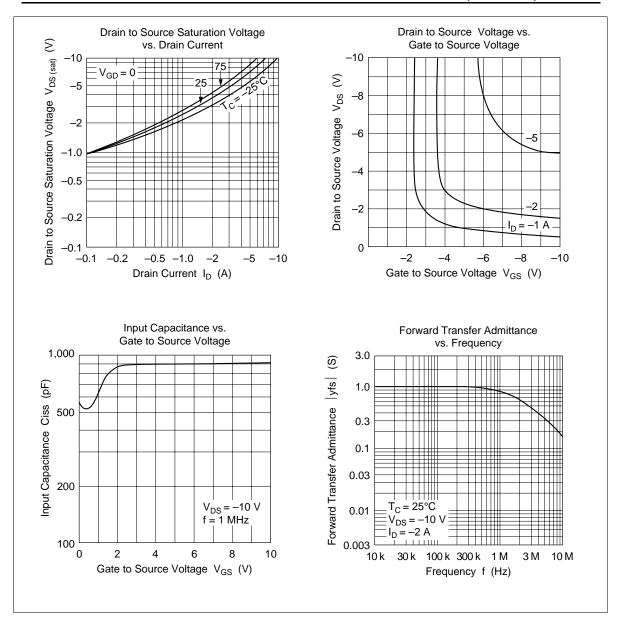
Note: 1. Value at $T_c = 25^{\circ}C$

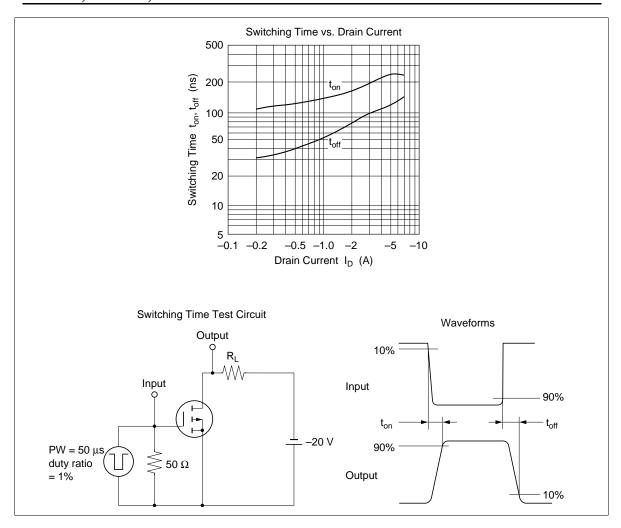
Electrical Characteristics ($Ta = 25^{\circ}C$)

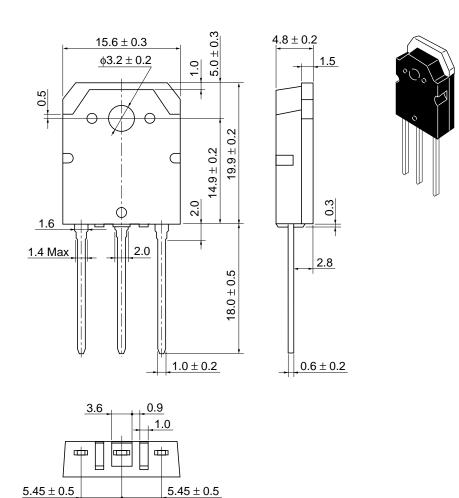
Item		Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source	2SJ160	$V_{(BR)DSX}$	-120	_	_	V	$I_D = -10 \text{ mA}$, $V_{GS} = 10 \text{ V}$
breakdown voltage	2SJ161		-140	_	_	V	_
	2SJ162		-160	_	_	V	_
Gate to source brea voltage	kdown	$V_{(BR)GSS}$	±15	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source cuto	ff voltage	$V_{GS(off)}$	-0.15	_	-1.45	V	$I_D = -100 \text{ mA}, V_{DS} = -10 \text{ V}$
Drain to source saturation voltage		$V_{\text{DS(sat)}}$	_	_	–12	V	$I_D = -7 \text{ A}, V_{GD} = 0^{*1}$
Forward transfer ad	mittance	y _{fs}	0.7	1.0	1.4	S	$I_D = -3 \text{ A}, V_{DS} = -10 \text{ V}^{*1}$
Input capacitance		Ciss	_	900	_	pF	$V_{GS} = 5 \text{ V}, V_{DS} = -10 \text{V},$
Output capacitance		Coss	_	400	_	pF	f = 1 MHz
Reverse transfer capacitance		Crss	_	40	_	pF	_
Turn-on time		t _{on}	_	230	_	ns	$V_{DD} = -20 \text{ V}, I_{D} = -4 \text{ A}$
Turn-off time		t _{off}	_	110	_	ns	

Note: 1. Pulse test









Unit: mm

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Semiconductor & Integrated Circuits. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

NorthAmerica http:semiconductor.hitachi.com/

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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose CA 95134 Tel: <1> (408) 433-1990 Fax: <1>(408) 433-0223 Hitachi Europe GmbH Electronic components Group Dornacher Stra§e 3 D-85622 Feldkirchen, Munich Germany

Tel: <49 > (89) 9 9180-0 Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead

Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533

Hitachi Asia Ltd. Taipei Branch Office

3F, Hung Kuo Building. No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218 Fax: <852> (2) 730 0281 Telex: 40815 HITEC HX

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